



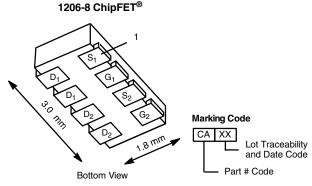
Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
30	0.085 at V _{GS} = 10 V	± 3.9		
	0.143 at V _{GS} = 4.5 V	± 3.0		

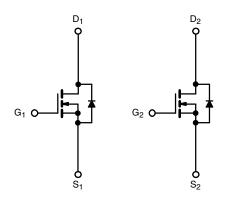
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si5902DC-T1-E3 (Lead (Pb)-free) Si5902DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C) ⁸	T _A = 25 °C	- I _D	± 3.9	± 2.9		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		± 2.8	± 2.1	1	
Pulsed Drain Current		I _{DM}	± 10		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.8	0.9		
Mariana Barra Brain di ad	T _A = 25 °C	P _D	2.1	1.1	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.1	0.6	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260		1 C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lumation to Analismati	t ≤ 5 s	- R _{thJA}	50	60	°C/W
Maximum Junction-to-Ambient ^a	Steady State		90	110	
Maximum Junction-to-Foot	Steady State	R _{thJF}	30	40	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See reliability manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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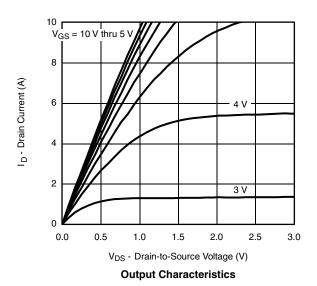
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1		
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 85 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V, I _D = 2.9 A	A		0.085	Ω	
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 2.2 A		0.120	0.143		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 2.9 A		20		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 0.9 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			5	7.5		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 2.9 \text{ A}$		0.8		nC	
Gate-Drain Charge	Q_{gd}			1.0			
Turn-On Delay Time	t _{d(on)}			7	11		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		12	18		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		12	18	ns	
Fall Time	t _f			7	11		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.9 A, dI/dt = 100 A/μs		40	80		

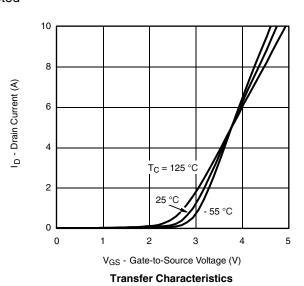
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



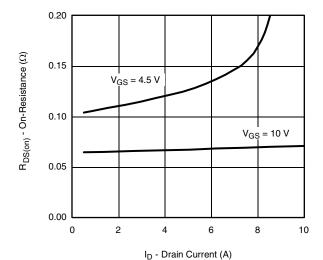




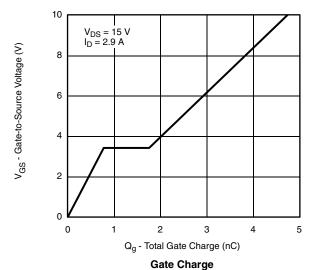


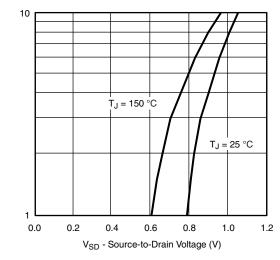


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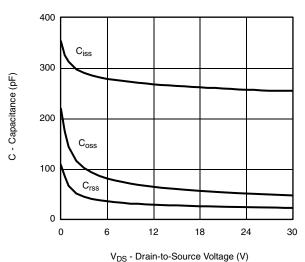


On-Resistance vs. Drain Current

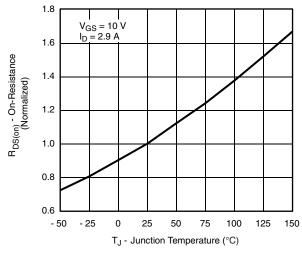




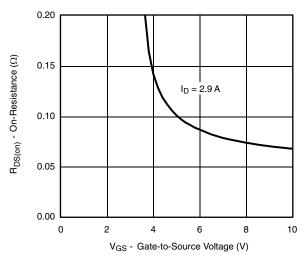
Source-Drain Diode Forward Voltage







On-Resistance vs. Junction Temperature



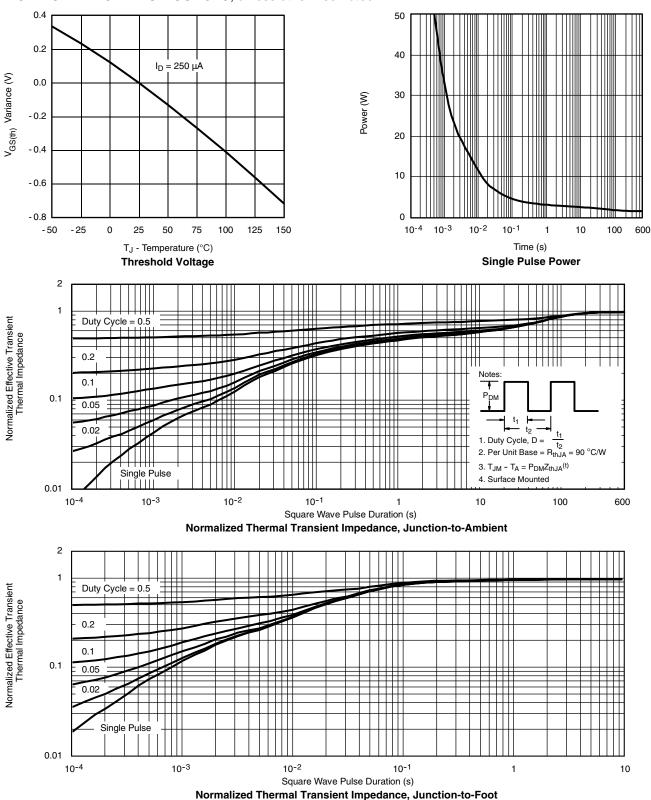
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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